

BRCS120N03ZJ

Rev.B Sep.-2020

描述 / Descriptions

DFN 2*2B-6L 塑封封装 N 沟道 MOS 场效应管。

N-Channel Enhancement Mode Field Effect Transistor in a DFN 2*2B-6L Plastic Package.

特征 / Features

$V_{DS} (V) = 30V$

$I_D = 8 A (V_{GS} = \pm 20V)$

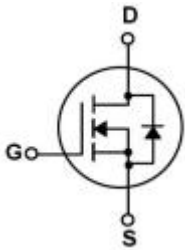
无卤产品。HF Product.

用途 / Applications

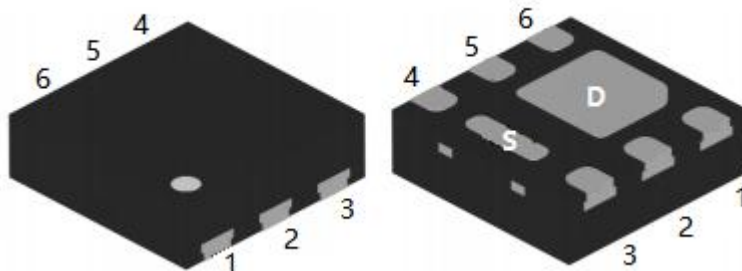
用于低压电路如：汽车电路、DC/DC 转换、便携式产品的电源高效转换。

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



出脚	定义
Pin1	D
Pin2	D
Pin3	G
Pin4	S
Pin5	D
Pin6	D

放大及印章代码 / hFE Classifications & Marking

见印章说明。See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	30	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	8	A
Gate-Source Voltage	V_{GS}	± 20	V
Avalanche Current	I_{AS}	12.9	A
Single Pulsed Avalanche Energy	E_{AS}	199	mJ
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	2.8	W
Junction Temperature Range	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$
Maximum Junction-to-Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	45
	Steady-State	$R_{\theta JA}$	80

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}$ $I_D=250\mu\text{A}$	30	34.7		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30\text{V}$ $V_{GS}=0\text{V}$			1.0	μA
		$V_{DS}=30\text{V}$ $T_J=150^\circ\text{C}$			50	
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20\text{V}$ $V_{DS}=0\text{V}$			± 0.1	μA
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$ $I_D=8.0\text{A}$		12.8	14	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$ $I_D=6.0\text{A}$		18	20	$\text{m}\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu\text{A}$	1	1.8	2.5	V
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}$ $I_F=1.0\text{A}$		0.7	1.2	V
Signal Source Resistance	R_g	$F=1\text{MHz}$		1.67		Ω
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}$ $V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		666		pF
Output Capacitance	C_{oss}			26		
Reverse Transfer Capacitance	C_{rss}			63		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=15\text{V}$ $V_{GS}=10\text{V}$ $R_L=1.9\Omega$ $R_{GEN}=3.0\Omega$		4.8		ns
Turn-On Rise Time	t_r			3.3		
Turn-Off Delay Time	$t_{d(off)}$			18.5		
Turn-Off Fall Time	t_f			4.0		

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Total Gate Charge	$Q_{g(10V)}$	$V_{DS}=15V$ $V_{GS}=10V$ $I_D=8.0A$		8.9		nC
Total Gate Charge	$Q_{g(4.5V)}$			4.3		
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			1.7		

电参数曲线图 / Electrical Characteristic Curve

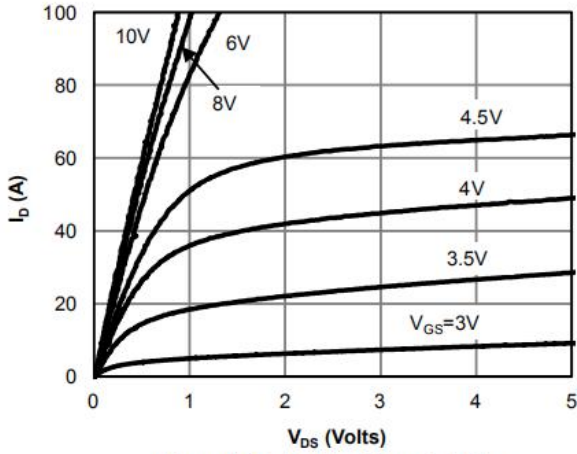


Figure 1: On-Region Characteristics

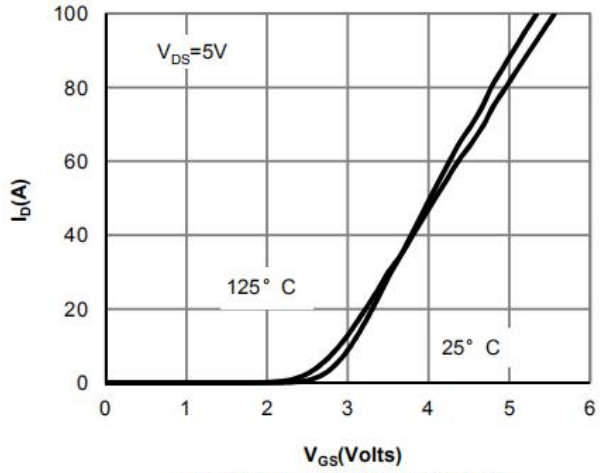


Figure 2: Transfer Characteristics

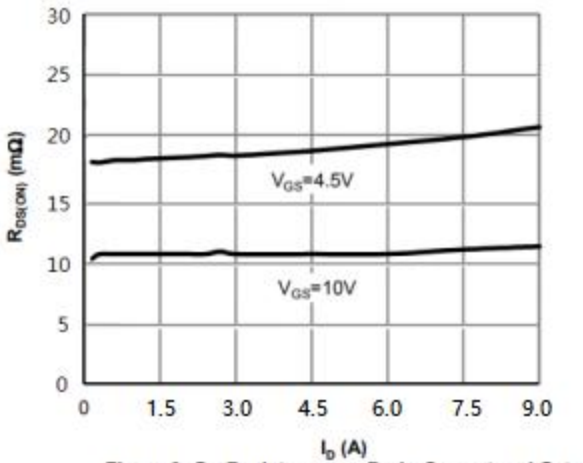


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

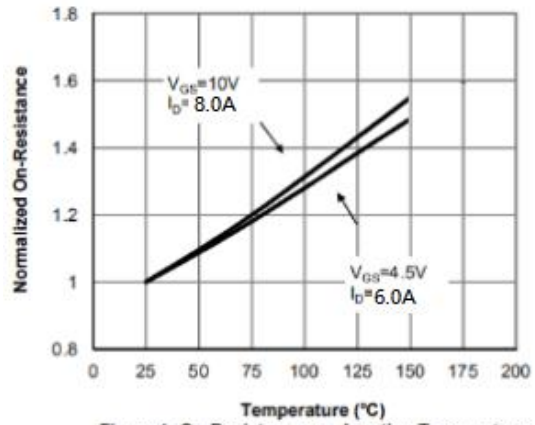


Figure 4: On-Resistance vs. Junction Temperature

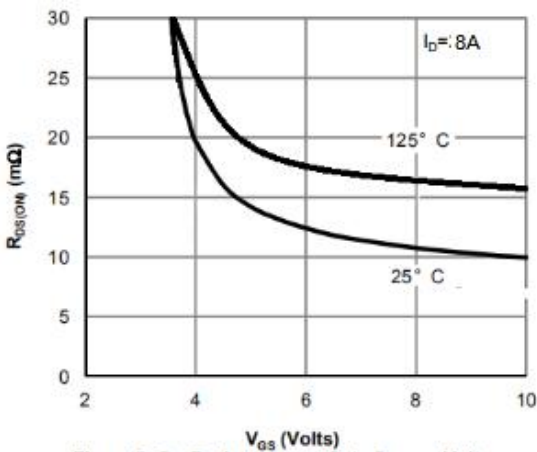


Figure 5: On-Resistance vs. Gate-Source Voltage

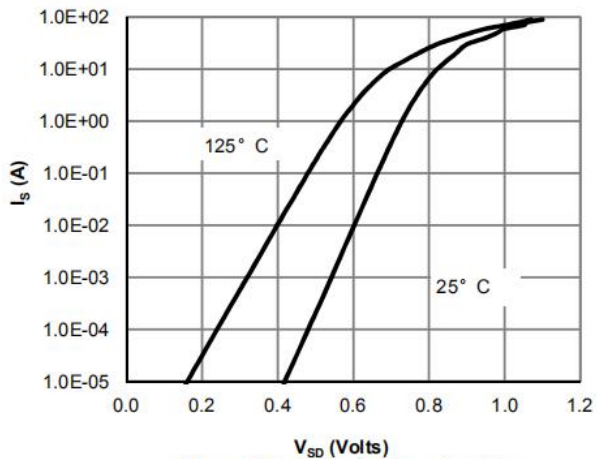


Figure 6: Body-Diode Characteristics

电参数曲线图 / Electrical Characteristic Curve

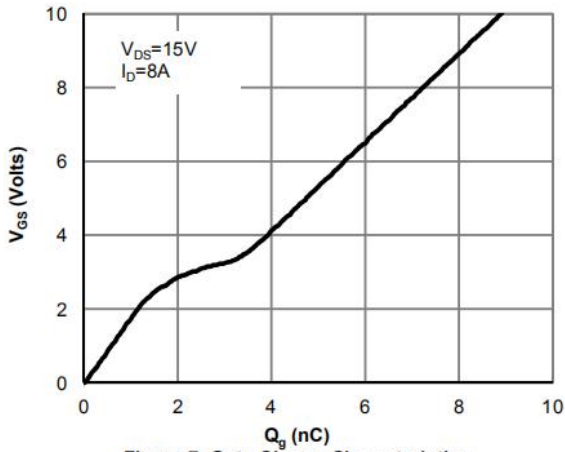


Figure 7: Gate-Charge Characteristics

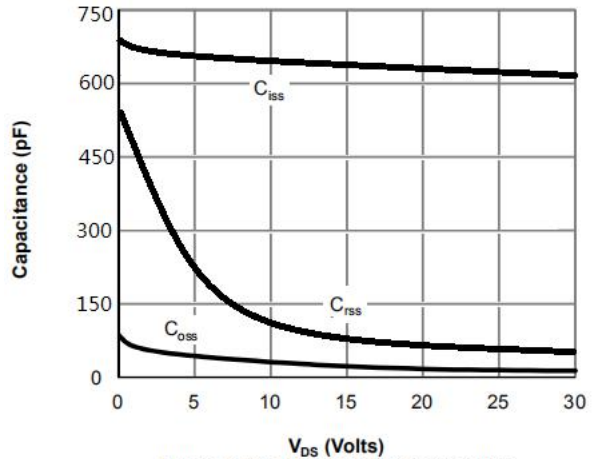


Figure 8: Capacitance Characteristics

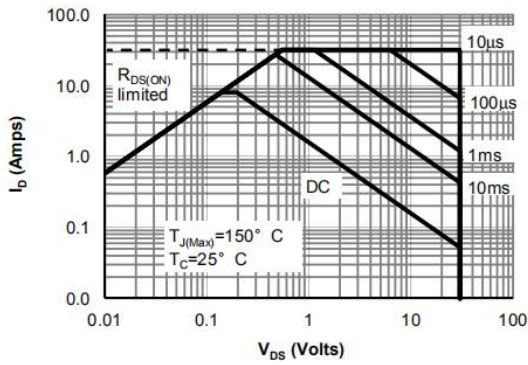


Figure 9: Maximum Forward Biased Safe Operating Area

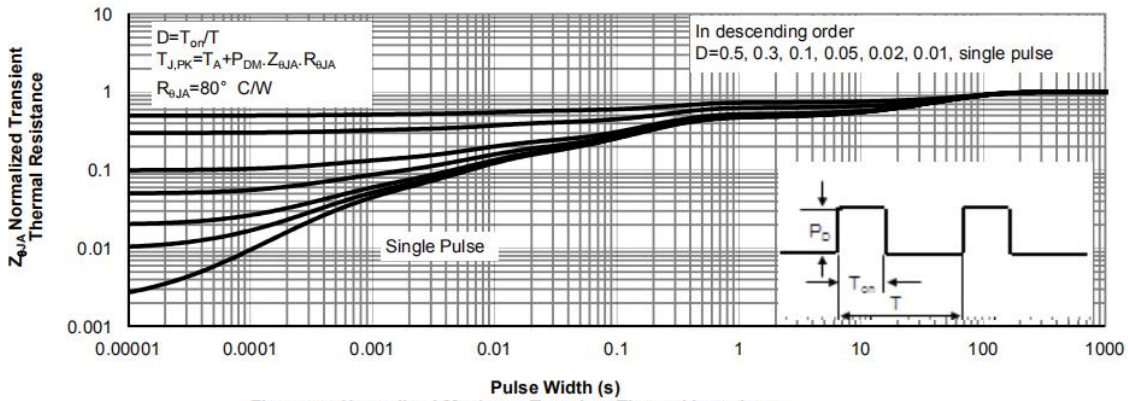


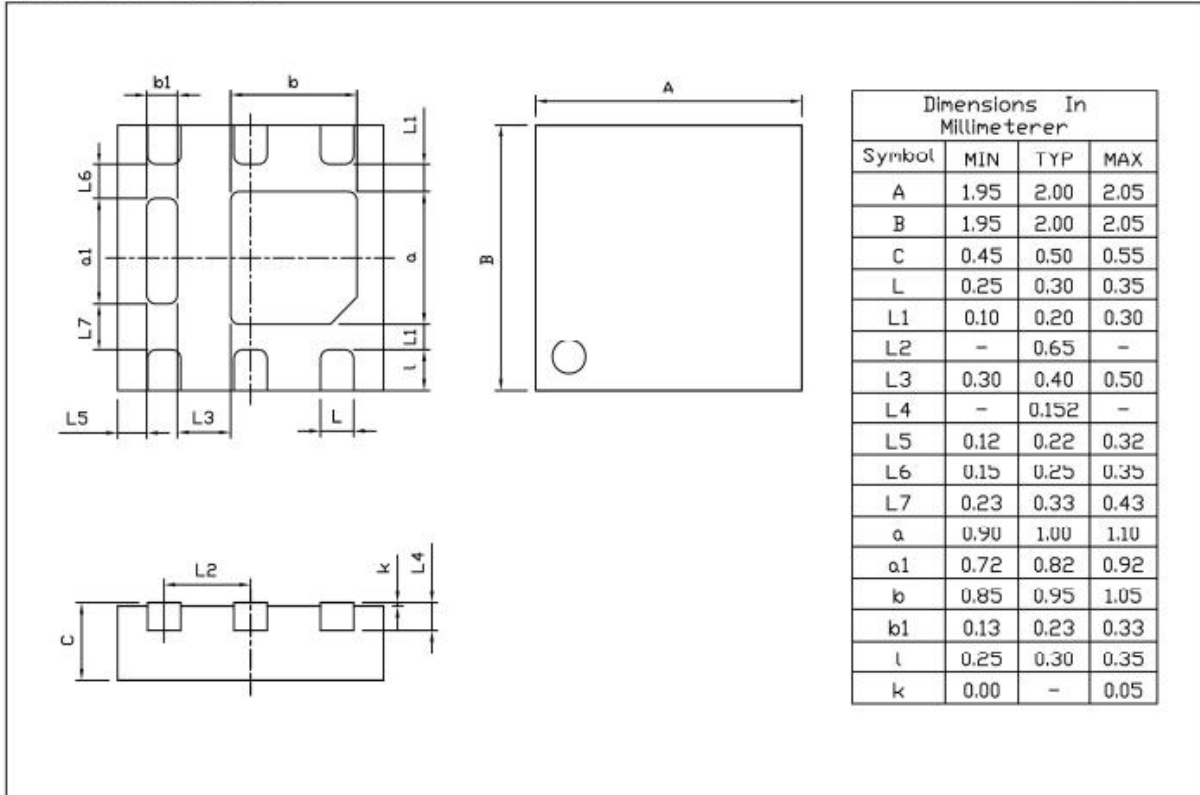
Figure 10: Normalized Maximum Transient Thermal Impedance

外形尺寸图 / Package Dimensions

DFN2×2B-6L-0.5 外形尺寸图

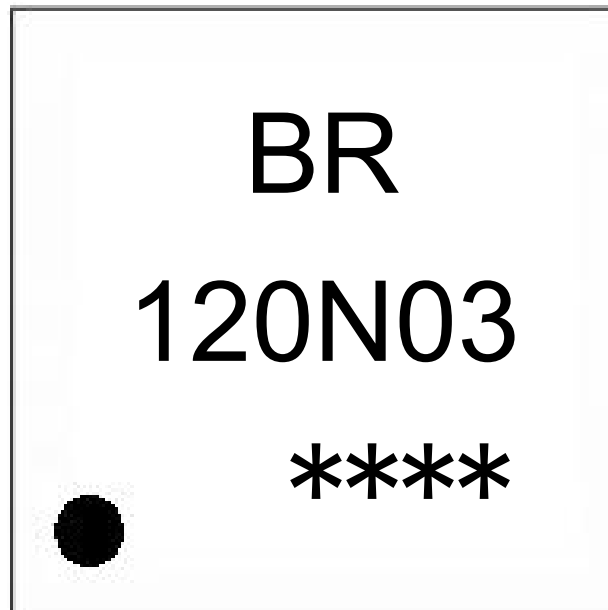
DFN2×2B-6L-0.5

Unit:mm



Rev.01 202006

印章说明 / Marking Instructions



说明:

BR: 为公司代码

120N03: 为型号代码

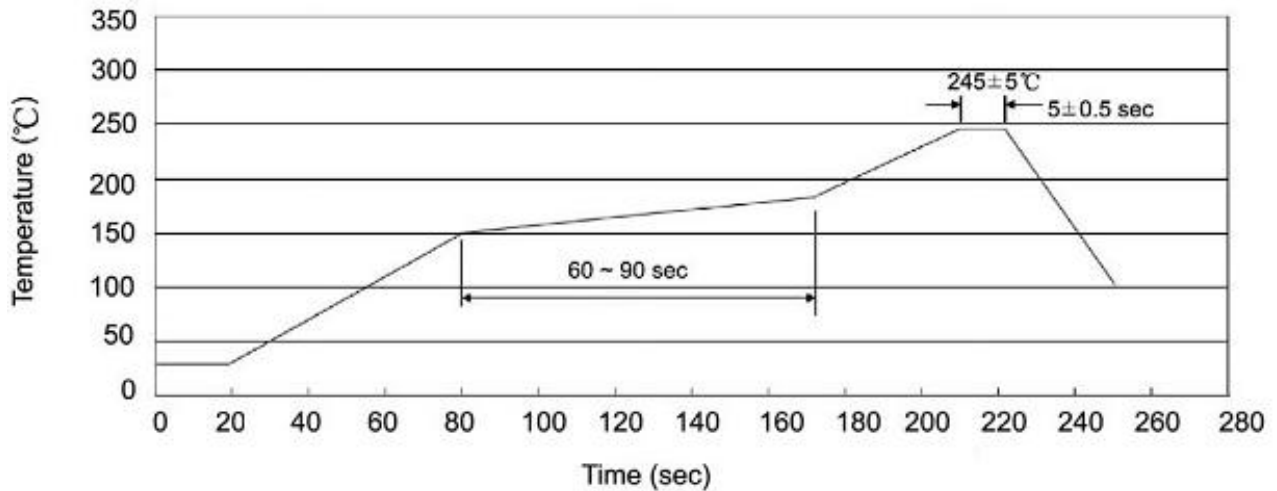
****: 为生产批号代码, 随生产批号变化。

Note:

BR: Company Code.

120N03: Product Type

****: Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)


说明:

- 1、预热温度 150~180°C, 时间 60~90sec;
- 2、峰值温度 245±5°C, 时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度: 260±5°C

时间: 10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
DFN 2*2B-6L	3,000	10	30,000	4	120,000	7" ×8	210×210×205	445×445×230

使用说明 / Notices

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